

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

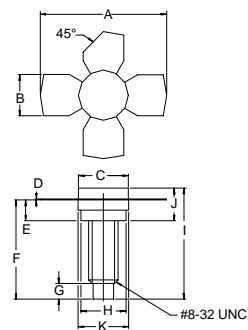
The **BFR96** is Designed for Class A Television Band IV- V Amplifier Applications Requiring High Linearity.

FEATURES:

- $P_G = 7.0$ dB Typical at 860 MHz
- $IMD_3 = -63$ dBc Typ. at $P_{REF} = 0.5$ W
- **Omnigold™** Metallization System

MAXIMUM RATINGS

I_C	75 mA
V_{CBO}	20 V
P_{DISS}	16 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$45^\circ C/W$

PACKAGE STYLE .280 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

ORDER CODE: ASI10784
CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0$ mA	15			V
BV_{CBO}	$I_C = 100$ μA	20			V
BV_{EBO}	$I_E = 100$ μA	3.0			V
I_{CBO}	$V_{CBO} = 10$ V			100	nA
h_{FE}	$V_{CE} = 10$ V $I_C = 50$ mA	25		250	---
C_{CB}	$V_{CB} = 10$ V $f = 1.0$ MHz		1.0	1.5	pF
$ S_{21} $	$V_{CE} = 10$ V $I_C = 50$ mA $f = 500$ MHz		1.0	1.5	pF